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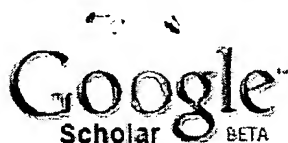
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 ... Pad size 2:85 mm  $\times$  11:5 mm 6:20 mm  $\times$  19:5 mm **Isolation** gap between pads 0:5 mm 0:5 mm ... There is a 0:5 mm **isolation** gap between pads. ...  
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 ... The "**parameter.inp**" file tends to contain **parameter** values that define en- vironments of the **simulation**, such as the domain size, boundary conditions on ...  
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... **parameters** are extracted from the layout and simulated again by SPICE. Power analysis is only one of many analysis SPICE can perform. Because SPICE **simulation** ...

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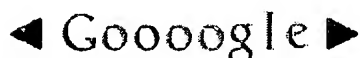
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 ... the circuit is created, actual dimen- sions and parasitic **parameters** are extracted ...  
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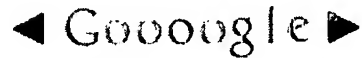
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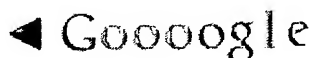
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